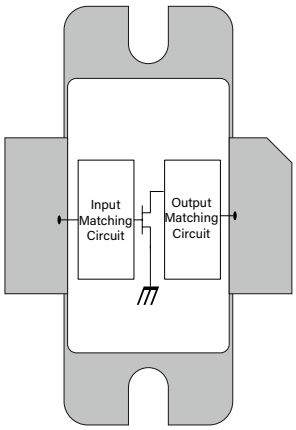
L-Band, GaN/SiC, RF Power Transistor

1.2 - 1.4 GHz | 650 W typ | 70% Efficiency typ | 15 dB Gain typ | 50 V | 2ms Pulse Length, 20% Duty Cycle

IGN1214L500B is a high power GaN-on-SiC RF power transistor that has been designed to suit the unique needs of modern long-pulse, long-range radar systems. It supplies a minimum of 500 W of peak output power, with typically >15 dB of gain and 70% efficiency. It operates from a 50 V supply voltage. For optimal thermal efficiency, the transistor is housed in a metal-based package with an epoxy-sealed ceramic lid.



FEATURES

- GaN on SiC HEMT Technology
- Output Power >500 W
- Pre-matched Input and Output Impedance
- High Efficiency - up to 75%
- 100% RF Tested Under 2ms, 20% duty cycle pulse conditions
- RoHS and REACH Compliant

APPLICATIONS

- L-band Radar Systems

Table 1. Absolute Maximum Ratings (Not Simultaneous)

Parameter	Symbol	Value	Units	Test Conditions
DC Drain-Source Voltage	V_{DS}	160	V	25 °C
DC Gate-Source Voltage	V_{GS}	-8 to +1.5	V	25 °C
DC Drain Current	I_D	48	A	25 °C
DC Gate Current	I_G	4.8	mA	25 °C
RF Input Power	$P_{RF,IN}$	25	W	25 °C
Operating Channel Temperature	T_{CH}	-55 to +225	°C	
Storage Temperature	T_{STG}	-55 to +150	°C	
Soldering Temperature	T_{SOLDER}	260 for 60s	°C	

Note: Operation outside the limits given in this table may cause permanent damage to the transistor

Table 2. DC Electrical Characteristics (Case temperature = 25 °C unless otherwise stated)

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Gate Pinch-Off Voltage	V_P	-5.0			V	V_{DS} = 50V, I_{DS} = 1mA
Quiescent Gate Voltage	V_Q		-2.6		V	V_{DS} = 50V, I_{DS} = 200mA

Table 3. RF Electrical Characteristics (Case temperature = 30 °C unless otherwise stated)

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
RF Input Power	$P_{IN, RF}$	11.2	16.0	17.5	W	P_{OUT} = 500W f = 1.2, 1.3, 1.4 GHz 2ms pulse length 20% duty cycle pulse conditions V_{DS} = 50V, I_{DS} = 200mA
Gain	G	14.5	15.0	16.5	dB	
Drain Efficiency	η	52	65	75	%	
Pulse Droop	D	-0.8	-0.4	+0.1	dB	
Input Return Loss	IRL	7	15	18	dB	
Load Mismatch Stability	VSWR-S	2:1				
VSWR Withstand	VSWR-LMT	3:1				

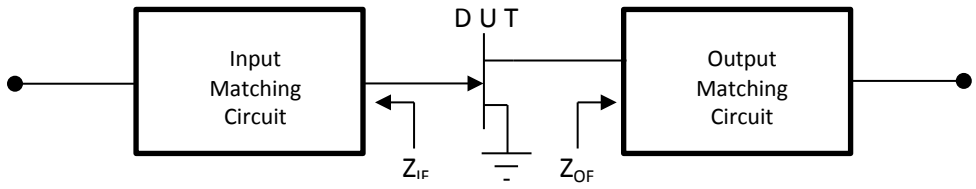
Note: Consult Integra Technologies Application Note 001 for information on how RF output power and pulse droop are measured.

Table 4. Thermal Resistance (Case temperature = 85 °C unless otherwise stated)

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Peak Thermal Resistance, Channel to Case	R_{TH}		0.45		°C/W	P_{DISS} = 269W 2ms pulse length, 20% duty cycle V_{DS} = 50V

Table 5. Test Fixture Source & Load Impedances (Case temperature = 25 °C unless otherwise stated)

Frequency (GHz)	Z_{IF}	Z_{OF}	Units	Test Conditions
1.2	1.8 - j 1.1	2.0 - j 1.8	Ω	P_{OUT} = 500W 2ms Pulse length, 20% Duty Cycle V_{DS} = 50V, I_{DS} = 200mA
1.3	2.0 - j 0.3	2.0 - j 1.6	Ω	
1.4	2.3 + j 0.4	1.9 - j 1.4	Ω	



TYPICAL PERFORMANCE

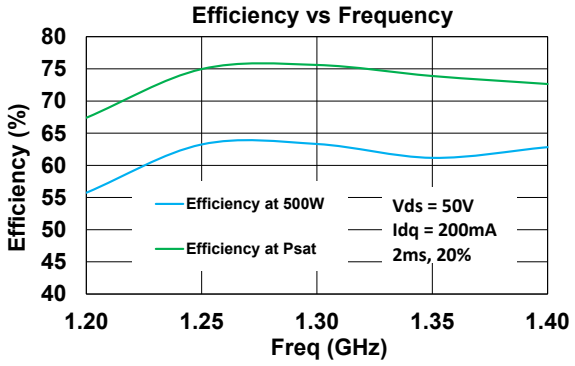


Figure 1

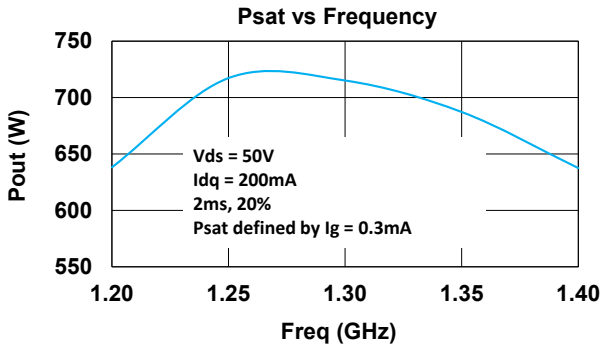


Figure 2.

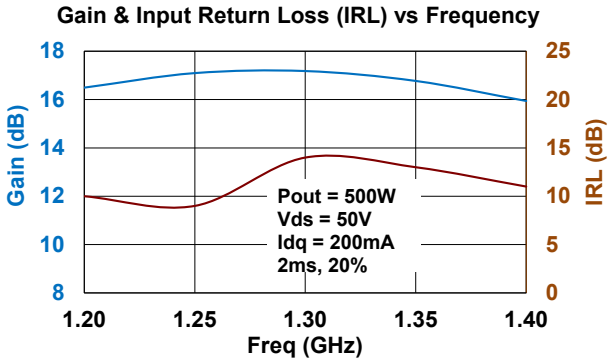


Figure 3

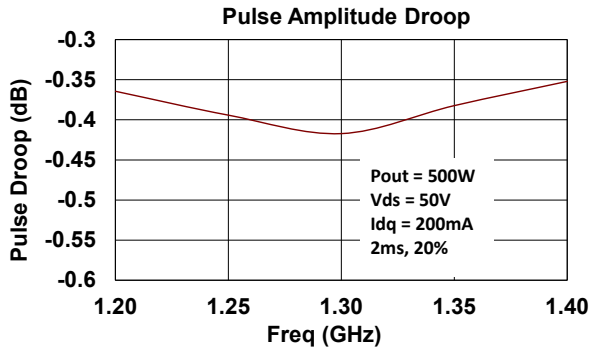
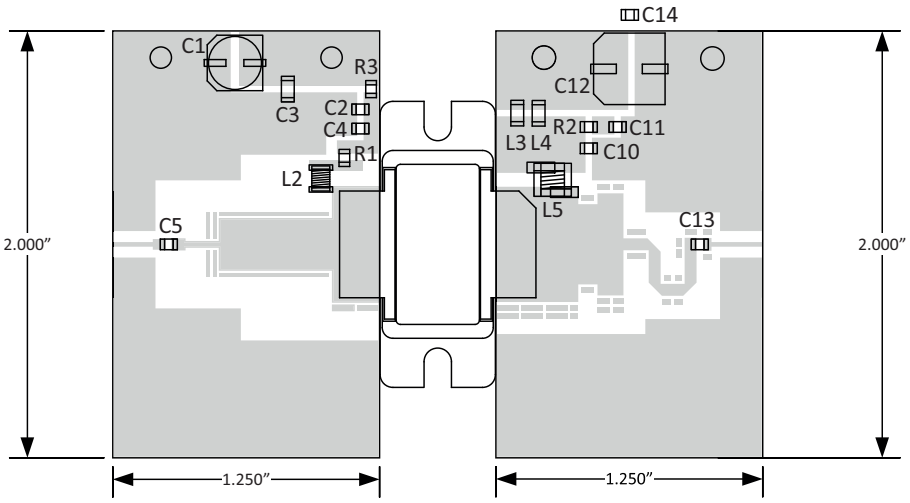


Figure 4.

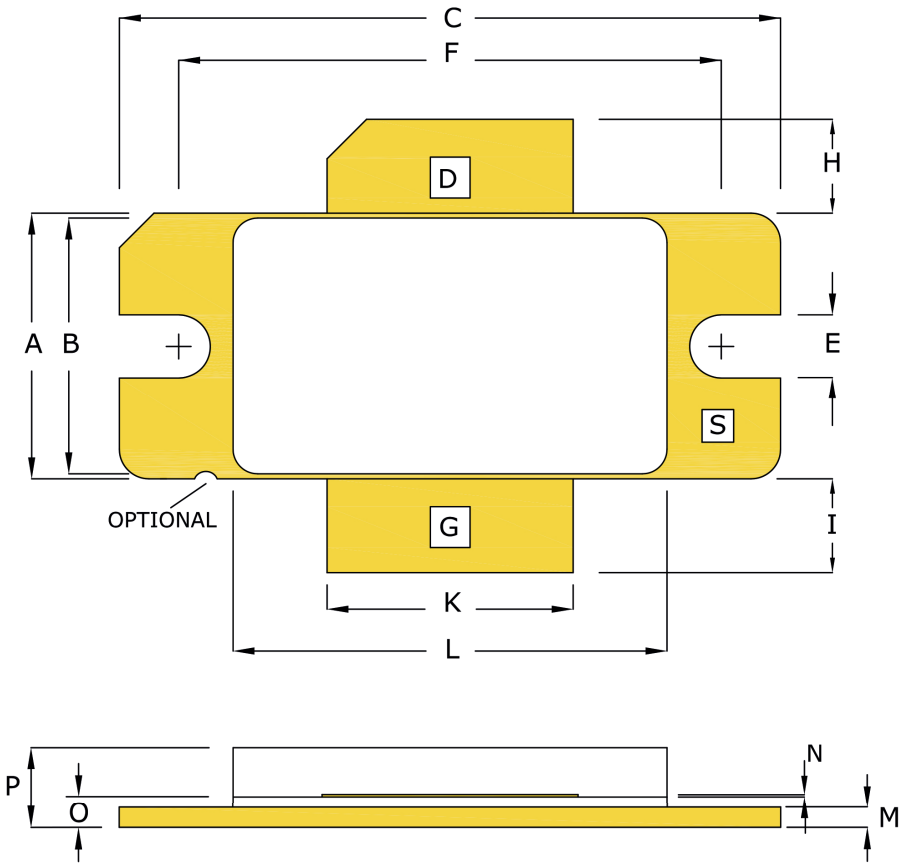
TEST FIXTURE



Bill of Materials for IGN1214L500B Test Fixture

Designator	Description	Quantity	Part Number
C1	CAP 47µF, 25V	1	AIEI
C2	CAP 1µF, 1206, 100V	1	
C3 ,C11	CAP 0.1µF, 0805, 50V	2	
C5, C13	CAP 18pF, Edge Mount	2	ATC600F180
C4, C10	CAP 18pF	2	ATC600F180
C12	CAP 68µF, 0810, 63V	1	AIEI
C14	CAP, 4700µF, 63V (mounted external to pcb)	1	
L2	IND 27.3nH, 0908SQ-27N	1	CC
L3, L4	IND FB, 33 OHM, 1206, 6A	2	Murata BLM31PG330SN1L
L5	IND, 18.5nH	1	CC A05T_L_J
R1, R2	RES, 10 OHM, 0805	2	
R3	RES, 200 OHM, 0805	1	
PC Board Type	ROGERS RT6110.2, 25mil, 1/1oz. Copper	2	

PACKAGE PL95A1



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.537	0.543	13.64	13.79
B	0.515	0.525	13.08	13.34
C	1.337	1.343	33.96	34.11
E	0.123	0.133	3.12	3.38
F	1.095	1.105	27.81	28.07
H	0.175	0.205	4.45	5.21
I	0.175	0.205	4.45	5.21
J	--	--	--	--
K	0.495	0.505	12.57	12.83
L	0.871	0.889	22.12	22.58
M	0.036	0.044	0.91	1.12
N	0.003	0.006	0.08	0.15
□	0.059	0.065	1.50	1.65
P	0.154	0.182	3.91	4.62

PIN	SCHEDULE
D	DRAIN
S	S□URCE
G	GATE

ESD & MSL Rating

Parameter	Rating	Standard
ESD Human Body Model (HBM)	TBD	ESDA/JEDEC JS-001-2012
ESD Charged Device Model (CDM)	TBD	JEDEC JESD22-C101F
Moisture Sensitivty Level (MSL)	Unlimited Shelf Life	IPC/JEDEC J-STD-020

RoHS Compliance

Integra Technologies, Inc declares that its GaN and LDMOS Transistor Products comply with EU Directive 2011/65/EU on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863/EU.

REACH Compliance

Integra Technologies supports EU Regulation number 1907/2006 concerning the Registration, Evaluation, Authorization, and Restriction of Chemicals (REACH) as these apply to Integra semiconductor products, development tools, and shipping packaging.

In support of the REACH regulation, Integra will:

- Inform customers and recipients of Integra product if they contain any substances that are of very high concern (SVHC) per the European Chemical Agency (ECHA) website.
- Notify ECHA if any Integra product that contains any SVHCs which exceed guidelines for REACH chemicals by weight per part number and for total content weight per year for all products produced in or imported to the European market.
- Cease shipments of product containing REACH Annex XIV substances until authorization has been obtained.
- Cease shipment of product containing REACH Annex XVII chemicals when restrictions apply.

Integra has evaluated its materials, BOMs, and product specifications and product and has determined that this transistor conforms to all REACH and SVHC regulations and guidelines. Integra has implemented actions and control programs that will assure continued compliance.

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DEFINITIONS:
DATA SHEET STATUS
Advanced Specification - This data sheet contains Advanced specifications.
Preliminary Specification - This data sheet contains specifications based on preliminary measurements and data.
Final Specification - This data sheet contains final product specifications.
MAXIMUM RATINGS Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.

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